

[illegible]

A cross-sectional view of a semiconductor device 100. The device consists of a substrate 10 with a top surface 105. A thin layer 50 is formed on the top surface 105. A patterned layer 20 is formed on the layer 50, with a central portion 21 and side portions 23. A layer 52 is formed on the top surface of the central portion 21 and the side portions 23. A layer 30 is formed on the top surface of the layer 52. A layer 201 is formed on the top surface of the layer 30. A layer 202 is formed on the top surface of the layer 201. The device is shown in a cross-section between points H and H'.

FIG. 3

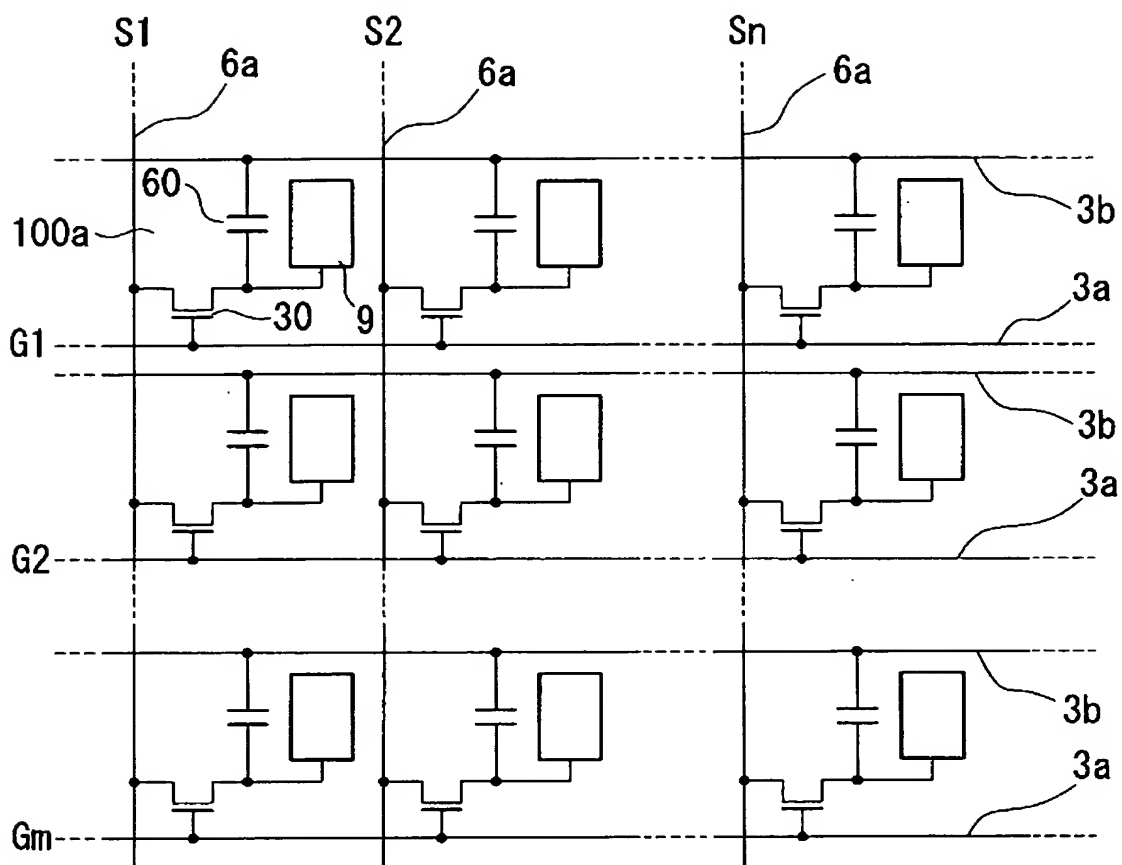


FIG. 4

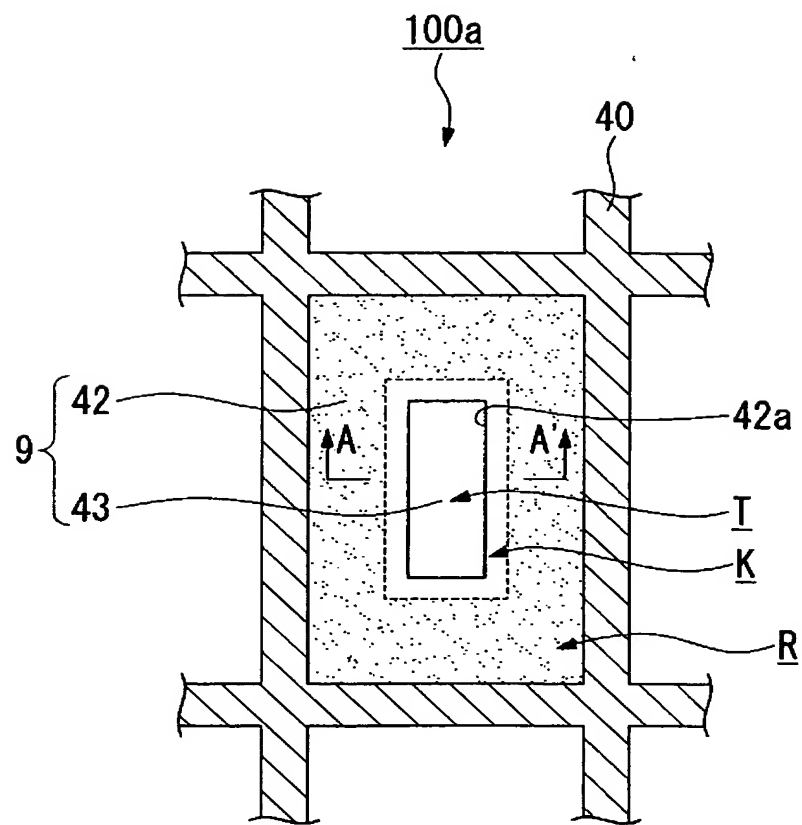


FIG. 5

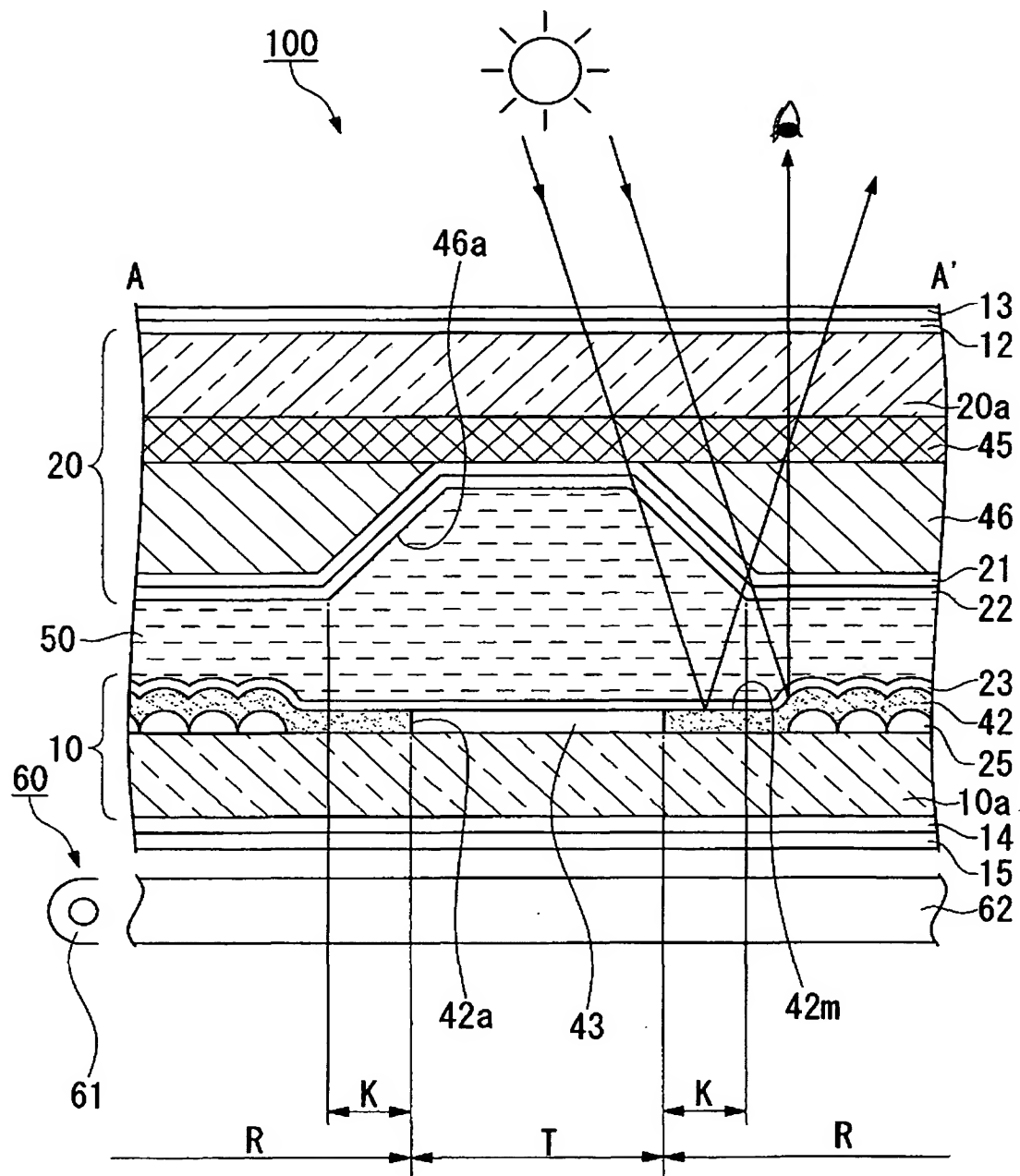


FIG. 6

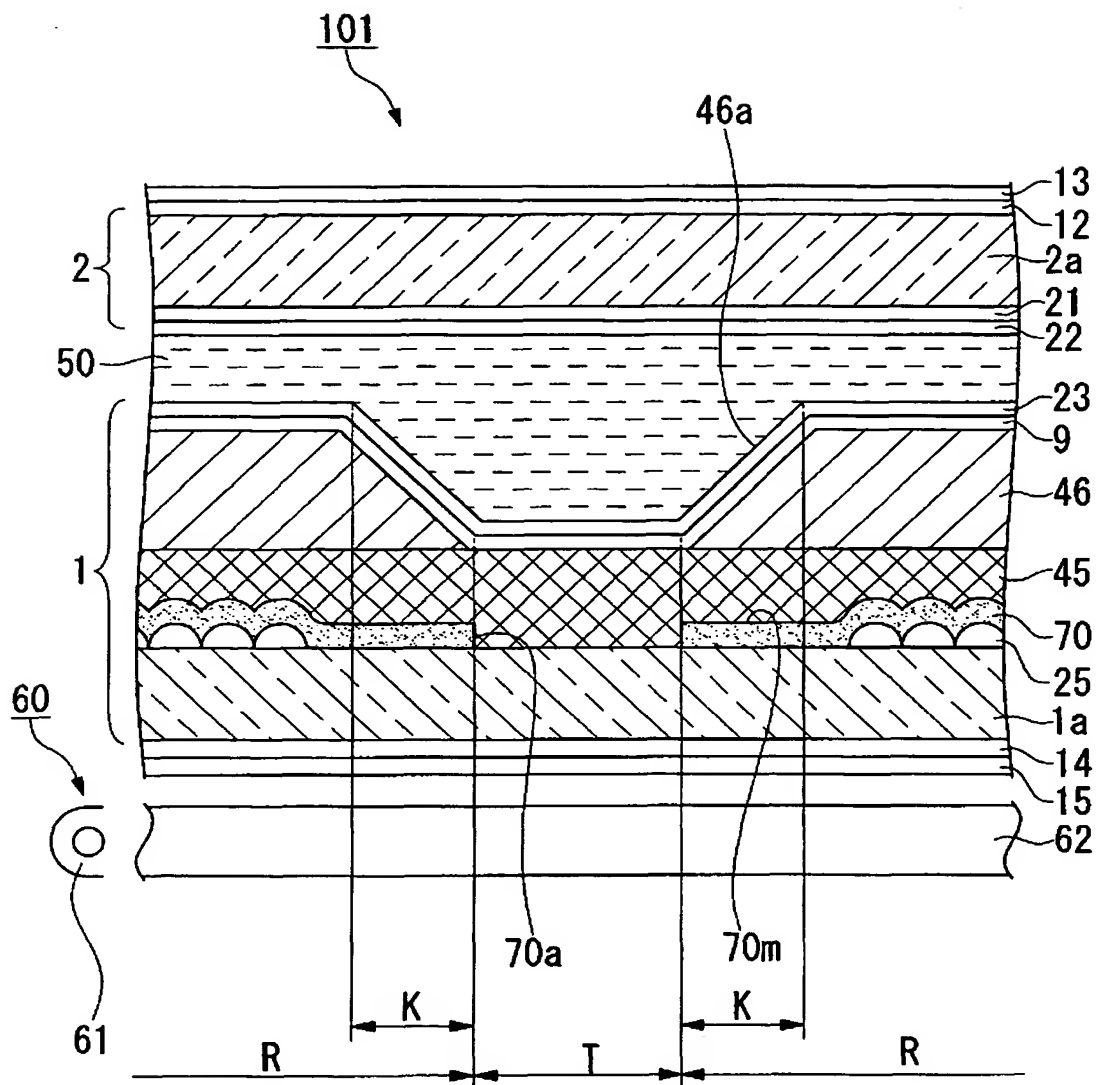


FIG. 7

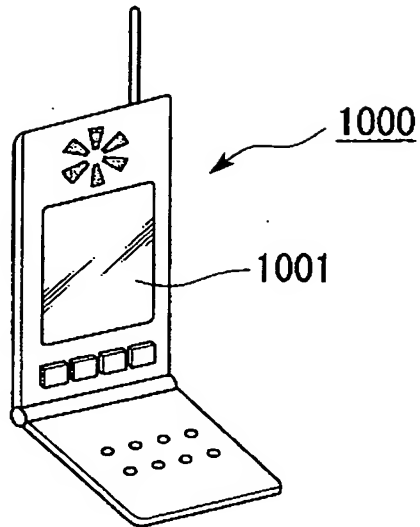


FIG. 8

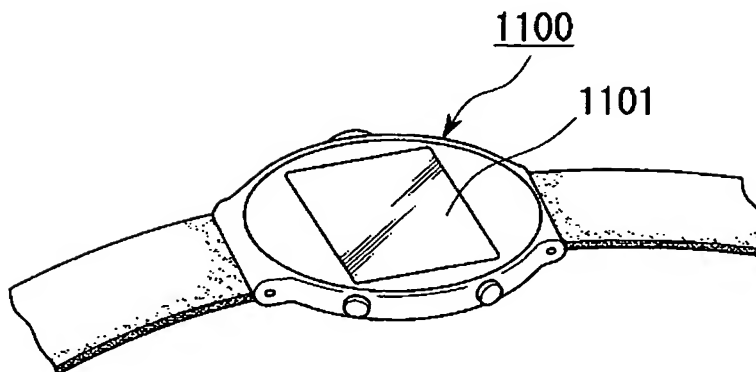


FIG. 9

